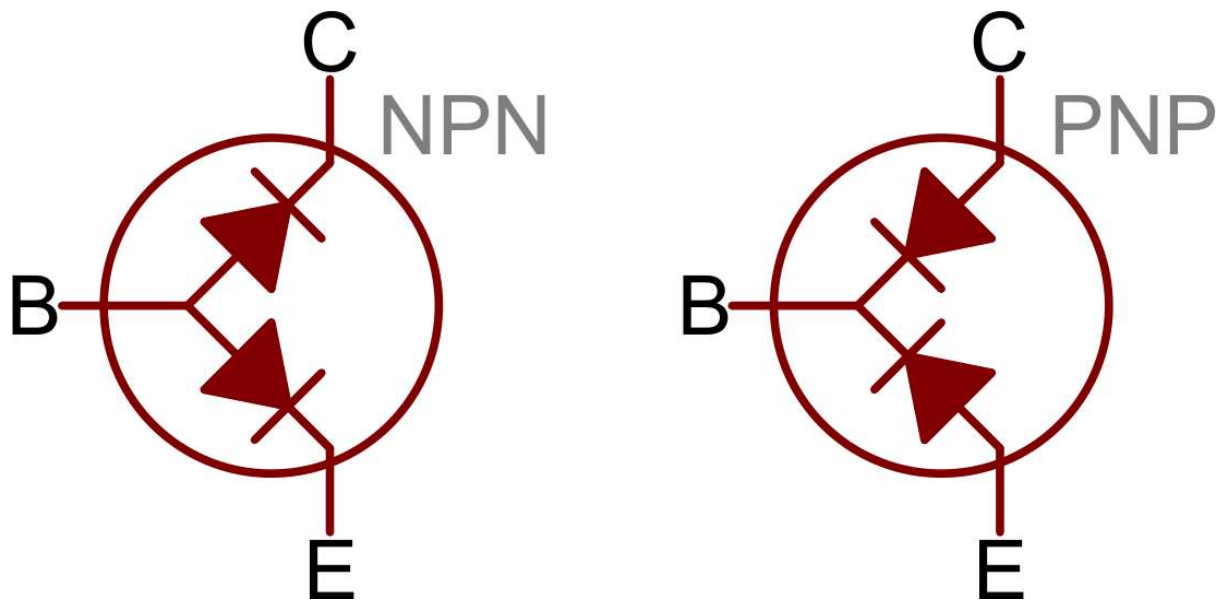


Chapter Two

Transistor as Switch



Chapter Outline: -

- 2.1 Bipolar Junction Transistor Switching Circuit
- 2.2 Type of BJT Switching Circuit
- 2.3 BJT Switching Times
- 2.4 BJT Switching Energy Losses
- 2.5 Summary
- 2.6 Exercises and Problems

2.1: Bipolar Junction Transistor Switching Circuit

Transistor switches can be used to switch a low voltage DC device (e.g. LED's) ON or OFF by using a transistor in its saturated or cut-off state.

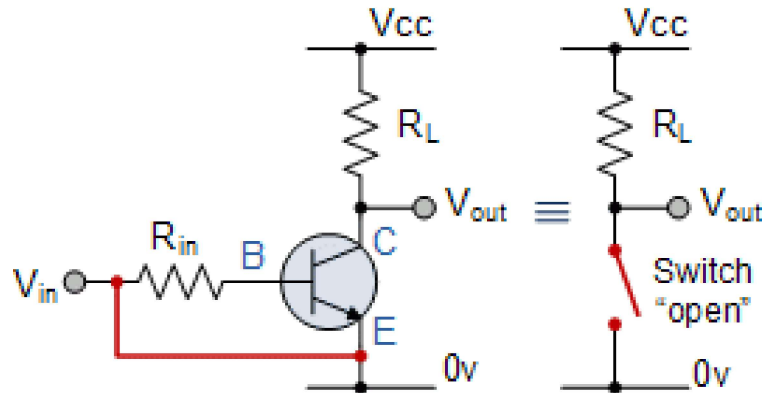


Fig. (2-1) Power switching circuits

The areas of operation for a transistor switch are known as the **Saturation Region** and the **Cut-off Region**. This means then that we can ignore the operating Q-point biasing and voltage divider circuitry required for amplification, and use the transistor as a switch by driving it back and forth between its “fully-OFF” (cut-off) and “fully-ON” (saturation) regions as shown below.

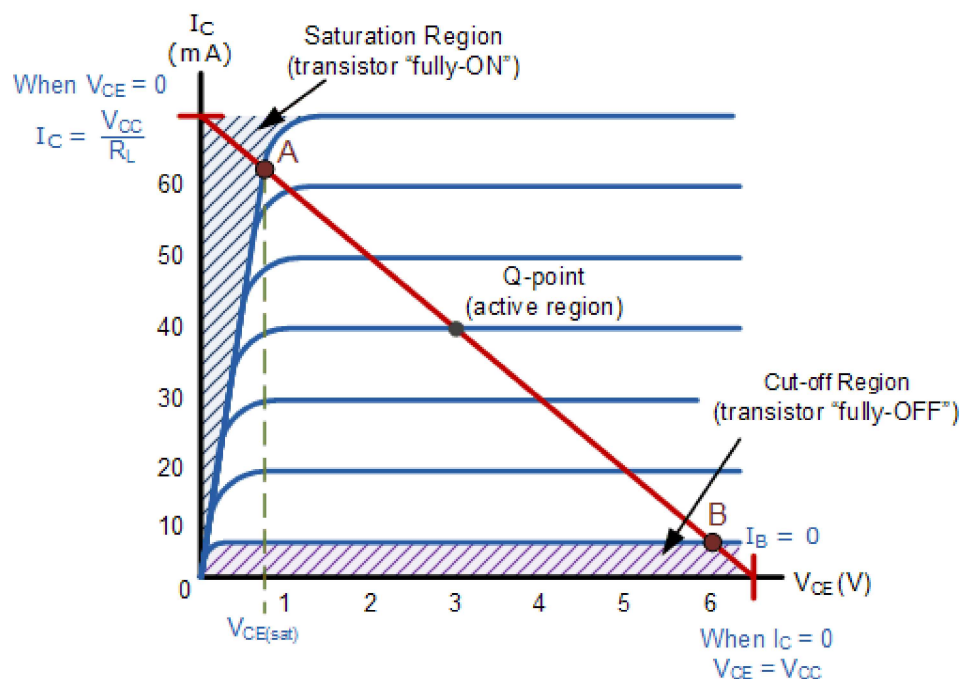


Fig. (2-2) Output characteristic curve of NPN common emitter BJT

2.2 Type of BJT Switching Circuit

2.2.1 Fully driven NPN BJT Switching Circuit

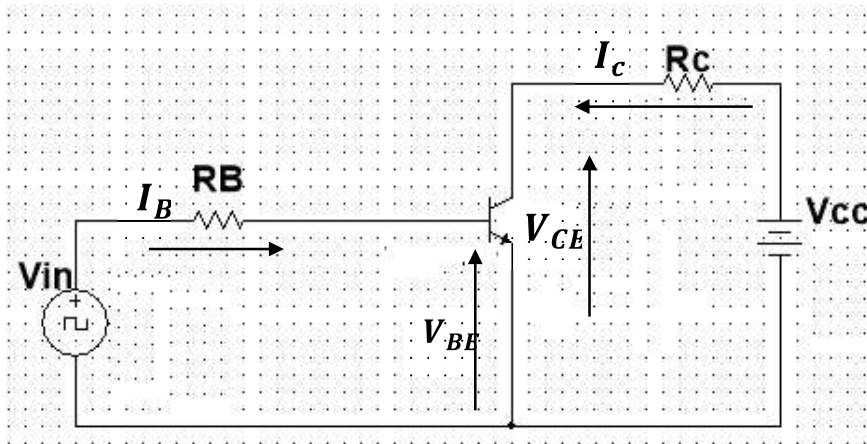


Fig. (2-3) Common emitter BJT fully driven switch

On-state: The BJT operate at the edge of the saturation region it's called point A in Fig.

$$V_{CE} = V_{CE(sat)}$$

$$I_c = I_{sat} = \frac{V_{cc} - V_{ce}}{R_c}$$

$$I_{Bmin} = \frac{I_{c(sat)}}{B_{dc}}, \text{ where } B_{dc} = \text{dc current gain of the BJT}$$

Condition of operation

$$I_B = 3 \times I_{Bmin}$$

I_{Bmin} = the minimum base current at which I_c has maximum saturated value

$$V_{in} = I_B R_B + V_{BE}$$

$$V_{BE} = 0.6 \text{ to } 0.7 \text{ volt}$$

Off-state: The BJT operate at the edge of the cutoff region its called point B in Fig.

$$I_B = 0$$

$$V_{CE} = V_{CC}$$

$$I_c = I_{CEO} = \text{leakage current}$$

2.2.2 Over driven NPN BJT Switching Circuit

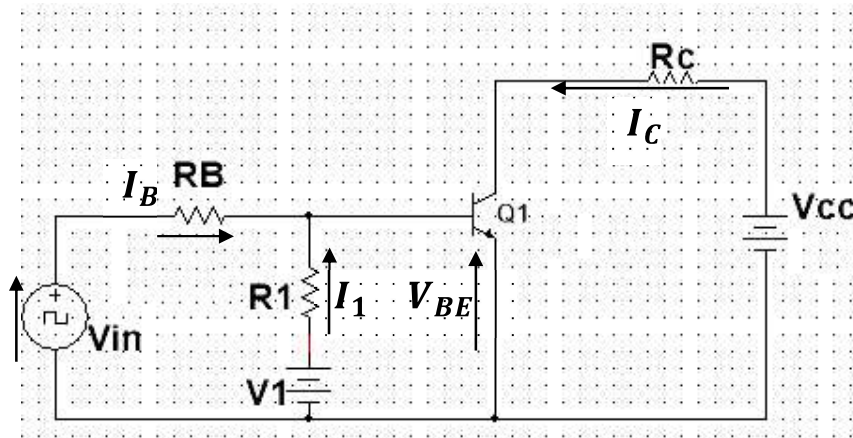


Fig. (2-4) Common emitter BJT Over driven switch

On-state: The BJT operate at the edge of the saturation region its called point \ddot{A} in Fig.

$$V_{CE} = 0$$

$$I_c = I_{max} = \frac{V_{cc}}{R_c}$$

$$I_{Bmin} = \frac{I_{max}}{B_{dc}}, \text{ where } B_{dc} = \text{dc current gain of the BJT}$$

Condition of operation

$$I_B = I_{Bmin}$$

$$I_1 = 2 \times I_B$$

I_{Bmin} = the minimum base current at which I_c has maximum saturated value

$$V_{in} = I_B R_B + V_{BE}$$

$$V_1 = I_1 R_1 + V_{BE}$$

Off-state: The BJT operate at the edge of the cutoff region its called point B in Fig.

$$I_B = 0$$

$$V_{CE} = V_{CC}$$

$$I_c = I_{CEO} = \text{leakage current}$$